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NTE5557 Silicon Controlled Rectifier (SCR) 820 Amp, TO200AB

Applications:

- DC Motor Control
- DC Power Supplies
- AC Controller

Absolute Maximum Ratings: ($T_J = +125^\circ\text{C}$ unless otherwise specified)

Repetitive Peak Voltages, V_{DRM} , V_{RRM}	1600V
Average On-State Current ($T_C = +55^\circ\text{C}$, 180°, Half Sine Wave, 50Hz), $I_{T(AV)}$	735A
RMS On-State Current ($T_{hs} = +55^\circ\text{C}$, Double Side Cooled), $I_{T(RMS)}$	820A
Continuous On-State Current ($T_{hs} = +25^\circ\text{C}$, Double Side Cooled), I_T	1230A
Peak One-Cycle Surge (10ms duration, Half Sine Wave, 50Hz), I_{TSM}	6200A
Peak On-State Voltage ($I_{TM} = 1500\text{A}$, $T_J = +25^\circ\text{C}$), V_{TM}	2.0V
Repetitive Peak Off-State Current (At V_{DRM}), I_{DRM}	40mA
Repetitive Peak Reverse Current (At V_{RRM}), I_{RRM}	40mA
Maximum Gate Current ($V_A = 12\text{V}$, $I_A = 1\text{A}$, $T_J = +25^\circ\text{C}$), I_{GT}	200mA
Maximum Gate Voltage ($V_A = 12\text{V}$, $I_A = 1\text{A}$, $T_J = +25^\circ\text{C}$), V_{GT}	3V
Rate of Rise of Off-State Voltage ($V_{DRM} = 1072\text{V}$), dv/dt	500V/ μs
Operating Junction Temperature, T_J	+125°C
Storage Temperature Range, T_{stg}	-40° to +125°C
Thermal Resistance, Junction-to-Case, R_{thJC}	0.05°C/W

